








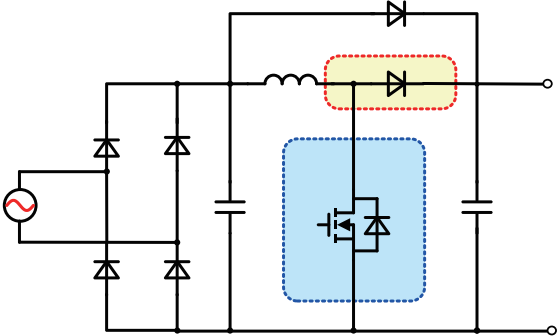
Si MOSFET Package type

億光Si功率元件具有成熟製造技術、可控性強、高耐壓、高可靠性等優點。億光Si功率元件系列產品，封裝型式為TO-Series。

Introducing the Everlight Si Power Devices, renowned for their mature manufacturing technology, exceptional controllability, high voltage tolerance, and outstanding reliability. The Everlight Si Power Device series encompasses a wide range of products, all packaged in the reliable and industry-standard TO-Series format.

Product Name	TO-220-3L	TO-220F-3L	TO-252-2L	DFN 5x6	DFN 8x8
Dimension (mm)	10.11*28.78*4.5	10.16*28.97*4.7	6.6*10*2.3	5*6*0.95	8*8*0.95
Picture					
Application	手機充電器 Mobile Chargers 小家電產品 Small Household Appliances 汽車電子、工控、消費性電子、太陽能、風力發電、資料中心、照明、交通等產業 automotive electronics, industrial control, consumer electronics, solar power, wind power generation, data centers, lighting, transportation, and other industries				

Switching PSU & Adapter



SiC SBD Specifications

SBD						
Reverse Voltage[V]	Continuous Forward Current[A]	DFN 8x8 5L	TO-252-2L	TO-220-2L	TO-247-2L	TO-247-3L
650	2	●	●	●		
	4	●	●	●		
	6	●	●	●		
	8	●	●	●		
	10	●	●	●	●	
	16 (Dual)	●	●	●	●	●
	20 (Dual)			●	●	●
	40 (Dual)					●
1200	50				●	
	2			●		
	5			●	●	
	8			●		
	10 (Dual)			●	●	●
	12			●		
	15			●	●	
	20 (Dual)			●	●	●
	40 (Dual)					●
	50				●	

SiC MOSFET Specifications

MOSFET						
Drain-source Voltage[V]	Drain-source On-state Resistance(Typ.)[mΩ]	TO-220F-3L	TO-220-3L	TO-247-3L	TO-247-4L	TO-263-7L
650	30			●	●	
	60	●	●	●	●	
	100	●	●	●	●	
1200	20			●	●	●
	40			●	●	●
	60			●	●	●
	80			●	●	●
	100			●	●	●

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Semi-Power Device

ENABLING THE FUTURE

SiC SBD、SiC MOSFET、GaN Transistor、
Si MOSFET

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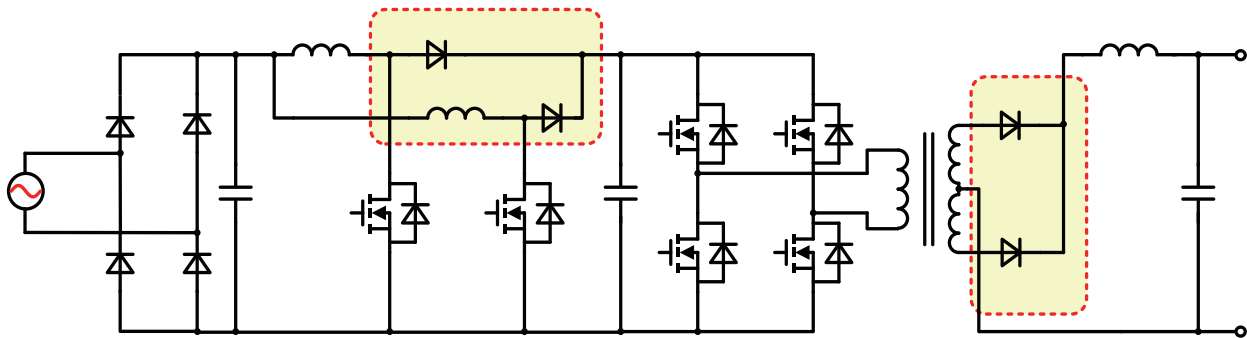
SiC SBD Package type

億光SiC二極體適用於高頻、高溫以及大功率應用場景，為新能源汽車與再生能源領域的首選材料。億光650V碳化矽二極體系列產品電流範圍涵蓋4A~20A，封裝型式為TO-Series。

Everlight's Silicon Carbide (SiC) Schottky Barrier Diodes (SBD) are the perfect choice for high-frequency, high-temperature, and high-power applications. These cutting-edge diodes are the preferred materials for the increasing demands of new energy vehicle and renewable energy sectors. With a voltage rating of 650V, the Everlight SiC SBD series offers a current range from 4A to 20A, ensuring optimal performance for your power needs. The diodes come in the TO-Series packages, known for its reliability and ease of use.

Product Name	TO-252-2L	TO-263-2L	TO-220-2L	TO-247-2L	TO-247-3L	DFN 8x8
Dimension (mm)	6.6*10*2.3	10.11*15*4.5	10.11*28.78*4.5	15.94*41.02*5.02	15.94*41.02*5.02	8*8*0.95
Picture						
Reverse Voltage [V]	650	650/1200	650/1200	1200	650/1200	650
Application	新能源汽車 New energy vehicle (NEV) 再生能源 Renewable energy 功率因數校正電路 Power factor correction circuit 逆變器 Inverter 不斷電系統 Uninterruptible power supply (UPS) DC-DC轉換器 DC-DC converter					

Server and Telecom



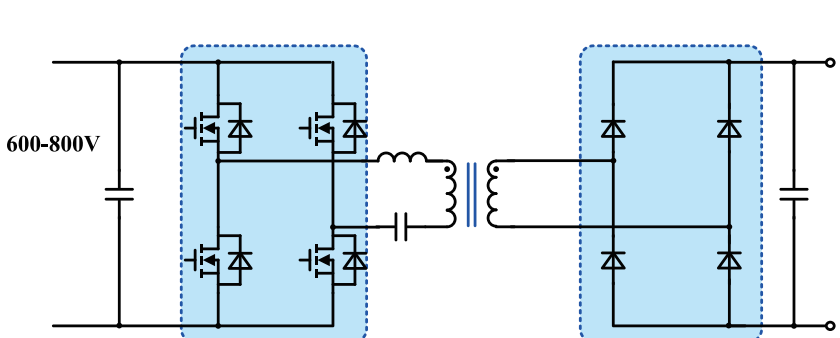
SiC MOSFET Package type

億光SiC MOSFET具有極快的開關速度且開關損耗低，是減少周邊器件使用、節省機構空間和成本的緊湊創新解決方案。億光650V/1200V SiC MOSFET系列產品電阻範圍涵蓋20 mOhm~100 mOhm，封裝型式為TO-Series。

The Everlight Silicon Carbide (SiC) MOSFETs come with ultra-fast switching speeds and minimal switching losses. These advanced MOSFETs from Everlight are the ideal compact solution to streamline your peripheral device usage, optimize space utilization, and reduce costs. The Everlight SiC MOSFET series covers voltage ratings of 650V and 1200V, offering a broad range of resistances, spanning from 20 mOhm to 100 mOhm. This ensures exceptional conductivity and efficiency for your power applications. Packaged in the reliable and widely adopted TO-Series format, these MOSFETs seamlessly integrate into your existing systems.

Product Name	TO-263-7L	TO-220-3L	TO-220F-3L	TO-247-3L	TO-247-4L	DFN 5x6	DFN 8x8
Dimension (mm)	10.2*15.5*4.5	10.11*28.78*4.5	10.16*28.97*4.7	15.94*41.02*5.02	15.94*41.02*5.02	5*6*0.95	8*8*0.95
Picture							
Drain-source Voltage[V]	650/1200	650	650	650/1200	650/1200	650	650
Application	伺服器、通信設備 Servers, communication equipment 不斷電系統 Uninterruptible power supply (UPS) 太陽能發電逆變器 Solar power inverter 電動車充電樁 Electric vehicle charging station						

AC/DC Charger



GaN Transistor Package type

億光GaN功率元件優勢為切換速度快、集成體積小，適用於替代中低壓矽基MOSFET在高頻的消費電子、新能源汽車等應用場景。億光GaN功率二極體系列產品電阻範圍涵蓋100 mOhm~300 mOhm，封裝型式為DFN。

Everlight Gallium nitride (GaN) Power Devices offer incredible advantages in terms of lightning-fast switching speeds and compact integration. These state-of-the-art GaN power devices from Everlight are the perfect replacement for medium to low voltage silicon-based MOSFETs in high-frequency applications such as consumer electronics and new energy vehicles. The Everlight GaN Power Diode series covers a wide range of resistances, spanning from 100 mOhm to 300 mOhm. This ensures exceptional conductivity and efficiency for your power applications. Packaged in the compact and reliable DFN format, these power diodes are designed to seamlessly fit into your existing systems.

Product Name	DFN 5x6	DFN 8x8
Dimension (mm)	5*6*0.95	8*8*1.3
Picture		
Drain-source Voltage[V]	650	650
Application	充電器 chargers 高頻率、高效率的電子產品 high-efficiency electronic products	

GaN Fast Charger

